

## 參考文獻

1. S. Nakamura, M. Senoh, N. Iwasa, and S. Nagahama, *Jpn. J. Appl. Phys., Part 2*(34), L797(1995).
2. S. Nakamura, T.Mokia, and M. Senoh, *Appl. Phys. Lett.* 64, 1689 (1994)
3. S. Nakamura, M. Senoh, N. Iwasa, S. Nagahama, T. Yamada, T.mat-sushita, Y. sugimoto, and H. Kiyodo, *Appl.Phys. Lett.* 70,868 (1996)
4. J.I. Pankove, E.A. Miller, and J.E. Berkeyheiser, *J. Lumin.* 5, 84 (1972)
5. W.Gotz, N.M. Johnson, J. Walker, D.P. Bour, and R.A. Street, *Appl. Phys. Lett.*68, 667,(1996)
6. Jin-Kuo Ho, Chang-Shyang Jong, Chien C. Chiu, Chao-Nien Huang, Chin-Yuen Chen, and Kwang-Kuo Shih *Appl. Phys.* Vol 74. Num 9 (1999)
7. 國立成功大學 材料工程學系 氧化鋅中介層對 ITO 透明導電膜性質的影響  
陳靜怡 91 年 6 月
8. Je-Hsiun Lan and Kanicki jerzy, "ITO Surface Ball Formation Induced by Atomic Hydrogen in PECVD and HW-CVD Tools", *Thin Solid Folms*, 304 (1997) 123
9. K. Zhang, F. Zhu, C.H. A. Huan and A.T.S. Wee, *J. Appl. Phys.*,86(1999) 974
10. L.J. Meng and M.P. dos Santos, *Thin Solid Films*, 303(1997)151
11. X.W. Sun, L.D. Wang and H.S. Kwok, *Thin Solid Films*, 360(2000) 75
12. R.B.H. Tahar, T.Ban, Y. Ohya and Y.Takahashi, *J. Appl. Phys.* 83 (1998) 2139
13. Watkins-Johnsons Co, *Thin Solid Films*, 221 (1992) 166
14. Wyckoff and W.G. Ralph., "Crystal Structure", Vol. 2, Chap. V, Illus., (1960) P.2.
15. 楊明輝, "金屬氧化物透明導電材料的基本原理", *工業材料*, 179 期, p.134
16. Lata Gupta, Abhai Mansingh, and P.K. Srivastava, *Thin Solid Films*, 176 (1989) 33
17. J.M. Poate, K.N. Tu and J.W. Mayer "Thin films-interdiffusion and reactions" (1978) P310

18. M.J. Howes and D.V. Morgan “Gallium Arsenide” chapter 6 (1986)
19. A.T. Ping, Q. Chen, J.W. Tang, M.A.Khan,I. Adesida, IEEE Electron Device Letters 19, 54 (1998)
20. W.Shockley in A. Goetzberger and R.M. Scarlett,”Research and Investigation of Inverse Epitaxial UHF Power Transistor”, ReP. No. AFAL-TDR-64-207, Air Force Avionics Lab., Wright-Patterson Air Force Base, Oh, Seot. 1964
21. Hadis Morkoc “Nitride Semiconductor and Devices” p196-197
22. G.S. Marlow and M.B. Das,Sol. Stat. Electro. 25,91 (1982)
23. L.F. Lester, J.M. Brown,J.C. Ramer, L.Zhang, and S.D. Hersee, Appl. Phys. Lett. 69, (1996) 2737
24. J. Venables, “Nucleation and Growth of Thin Films”, Rep. Prog. Phys., 47 (1984) 399
25. S. Honda, M. Watamori and K. Oura, Thin Solid Films 281-282 (1996) 206
26. C.J. Lee, S.K. Park, J.I. Han, W.K. Kim and M.G. Kwak “Korea Electronics Technology Institute, Pyungtaek, Kyunggi. 451-860, Korea
27. A.K. Kulkarni, K.H. Schulz, T.S. Lim, M. khan, Thin Solid Films, 345 (1999) 273
28. K. Tominaga, T. Ueda, T. Ao, M. Kataka and I. Mori, Thin Solid Films, 281-282(1996) 194
29. Shabbir A. Bashar, “Study of Indium Tin Oxide of Novel Optoelectronic Devices” 1998
30. 鄭好鈞 氮化鎵發光二極體 P 型金屬歐姆接觸特性及雷射剝離技術之研究 國立交通大學光電工程研究所 2002 年 6 月
31. Hadis Morkoc “Nitride Semiconductor and Devices” p 303
32. J.K.Sheu and Y.K. Su , Appl. Phys Vol 74, 1999, 16
33. D.W. Kim, Y.J. Sung, J.W. Park, G.Y. Yeom, Thin Solid Films 99 (2001) 82

34. D.S. Wu and Y.C. Lien , Appl. Phys. Vol 79, 2001, Num 18
35. 曾威揚 表面處理對 P 型氮化鎵歐姆接觸影響 國立清華大學材料工程研究所 92 年七月
36. I. Schnitzer and E. Yablonovich, Appl. Phys. Lett 63 ,1993, 16

